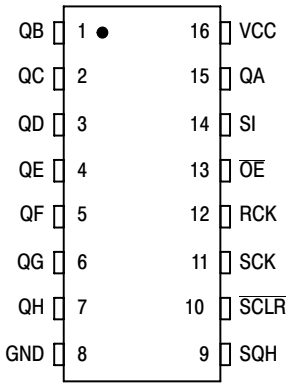


Figure 1. Pin Assignment (TSSOP−16)

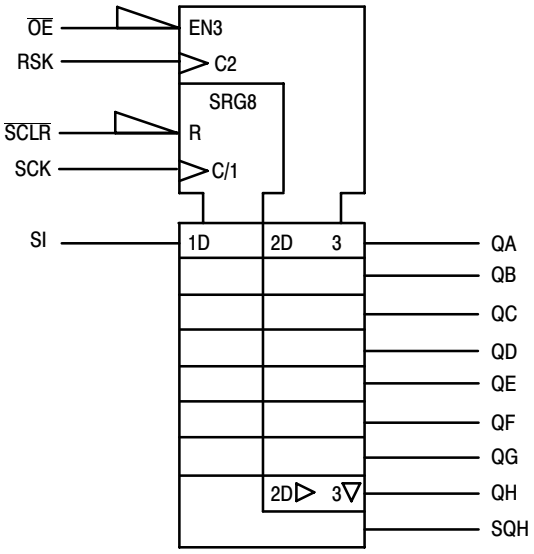


Figure 2. IEC Logic Symbol

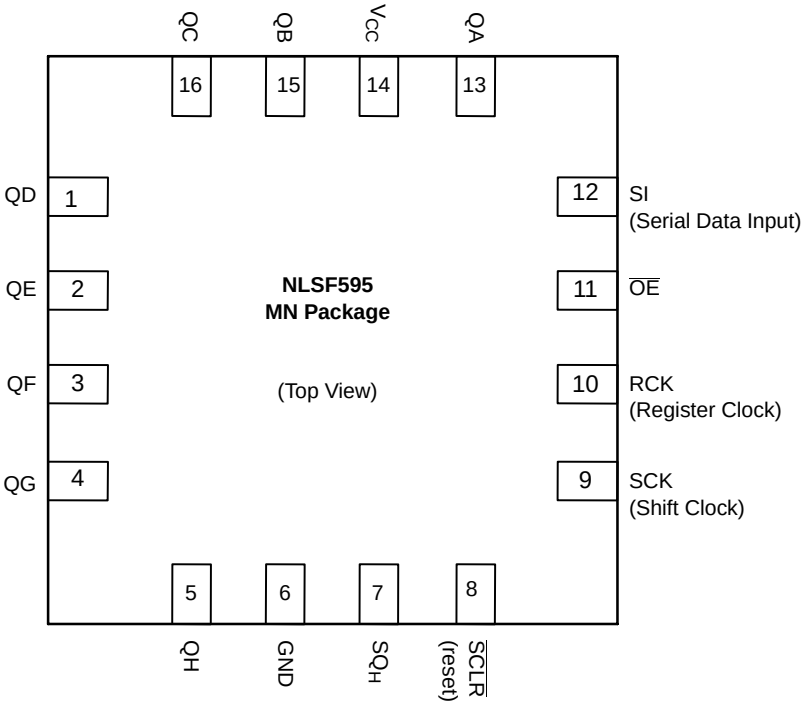


Figure 3. Pin Assignment (QFN−16)

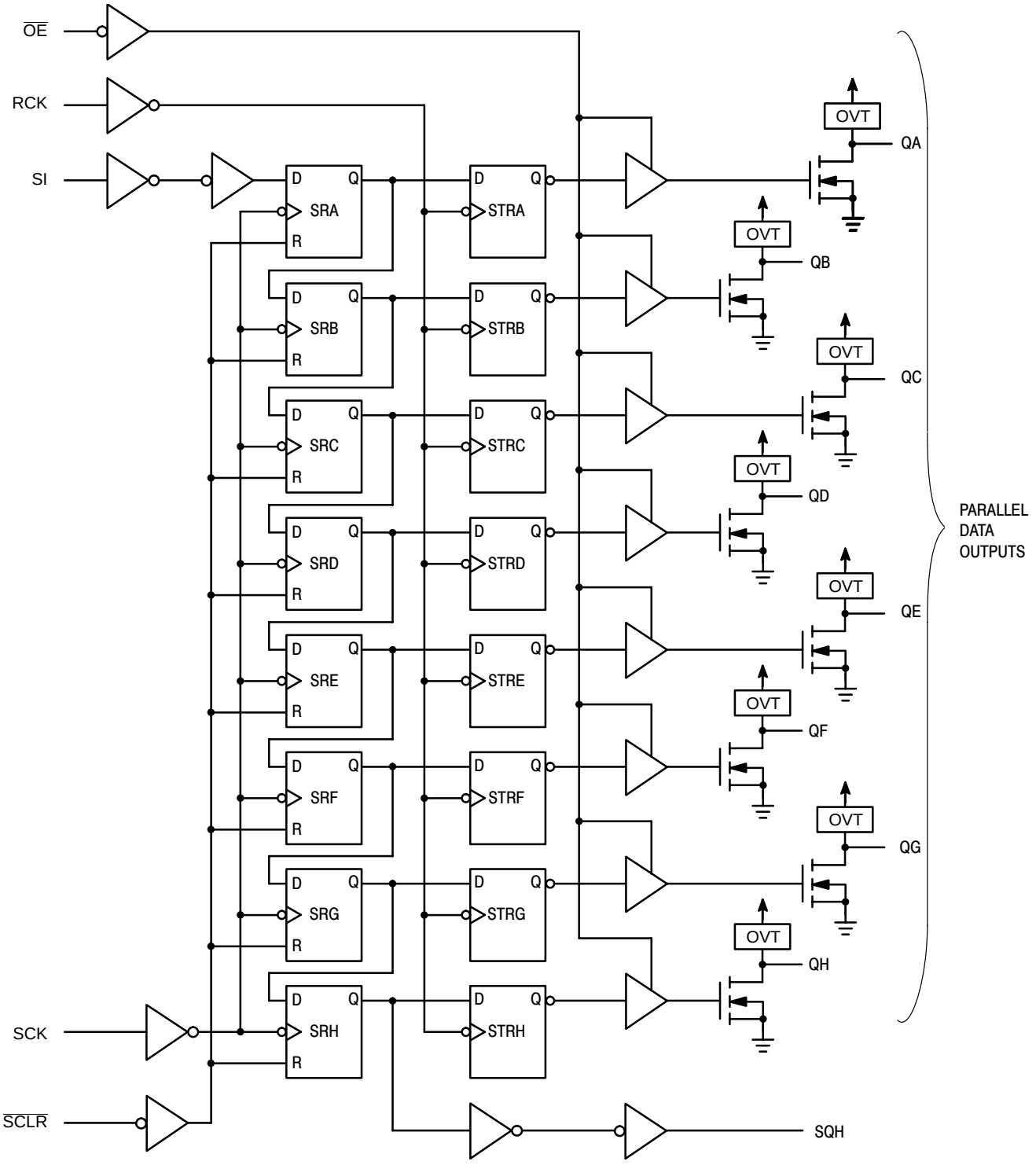


Figure 4. Expanded Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Positive DC Supply Voltage	−0.5 to +7.0	V
V_{IN}	Digital Input Voltage	−0.5 to +7.0	V
V_{OUT}	DC Output Voltage	−0.5 to V_{CC} +7.0	V
I_{IK}	Input Diode Current	−20	mA
I_{OK}	Output Diode Current	±50	mA
I_{OUT}	DC Output Current, per Pin	+50	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation in Still Air	450	mW
T_{STG}	Storage Temperature Range	−65 to +150	°C
$I_{LATCHUP}$	Latchup Performance Above V_{CC} and Below GND at 125°C (Note 1)	±300	mA
θ_{JA}	Thermal Resistance, Junction−to−Ambient	128	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage		0	V_{CC}	V
T_A	Operating Temperature Range, all Package Types		−55	125	°C
t_r, t_f	Input Rise or Fall Time	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0	50 15	ns/V

FUNCTION TABLE

Operation	Inputs					Resulting Function			
	Reset ($\overline{SCLR}$)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable ($\overline{OE}$)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA − QH)
Clear shift register	L	X	X	L, H, ↓	L	L	U	L	U
Shift data into shift register	H	D	↑	L, H, ↓	L	$D \rightarrow SR_A$; $SR_N \rightarrow SR_{N+1}$	U	$SR_G \rightarrow SR_H$	U
Registers remains unchanged	H	X	L, H, ↓	X	L	U	**	U	**
Transfer shift register contents to storage register	H	X	L, H, ↓	↑	L	U	$SR_N \rightarrow STR_N$	*	SR_N
Storage register remains unchanged	X	X	X	L, H, ↓	L	*	U	*	U
Enable parallel outputs	X	X	X	X	L	*	**	*	Enabled
Force outputs into high impedance state	X	X	X	X	H	*	**	*	Z

SR = shift register contents
STR = storage register contents
D = data (L, H) logic level
U = remains unchanged
↓ = High−to−Low
↑ = Low−to−High
* = depends on Reset and Shift Clock inputs
** = depends on Register Clock input

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			T_A = ≤ 85°C		T_A = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Minimum High−Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V_{IL}	Maximum Low−Level Input Voltage		2.0 3.0 4.5 5.5			0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65	V
V_{OH}	Minimum High−Level Serial Output Only Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} I_{OH} = − 50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V_{OL}	Maximum Low−Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	I_{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
V_{OL2}	Maximum Low−Level Output Voltage with Max. Load $V_{IN} = V_{IH}$ or V_{IL}	I_{OL} = 20 mA I_{OL} = 25 mA	3.0 4.5		0.8 0.5	1.0 0.6		1.1 0.7		1.25 0.8	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			± 0.1		±1.0		± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μA
I_{OZ}	Three−State Output Off−State Current QA−QH	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5			±0.25		±2.5		± 2.5	μA
I_{LKG}	Active (2) State Off Output Leakage Current QA−QH	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5			±0.25		±2.5		± 2.5	μA
I_{OFF}	Power Off Output Leakage All Outputs	V_{IN} = 0 or 5.5 V V_{OUT} = 5.5 V	0			±0.25		±2.5		± 2.5	μA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25°C$ Min	$T_A = 25°C$ Typ	$T_A = 25°C$ Max	$T_A \le 85°C$ Min	$T_A \le 85°C$ Max	$T_A \le 125°C$ Min	$T_A \le 125°C$ Max	Unit
f_{max}	Maximum Clock Frequency (50% Duty Cycle)	V_{CC} = 3.3 ± 0.3 V	80	150		70		70		MHz
		V_{CC} = 5.0 ± 0.5 V	135	185		115		115		
t_{PLH}, t_{PHL}	Propagation Delay, SCK to SQH	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF		8.8	13.0	1.0	15.0	1.0	15.0	ns
		C_L = 50 pF		11.3	16.5	1.0	18.5	1.0	18.5	
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF		6.2	8.2	1.0	9.4	1.0	9.4	
		C_L = 50 pF		7.7	10.2	1.0	11.4	1.0	11.4	
t_{PHL}	Propagation Delay, $\overline{SCLR}$ to SQH	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF		8.4	12.8	1.0	13.7	1.0	13.7	ns
		C_L = 50 pF		10.9	16.3	1.0	17.2	1.0	17.2	
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF		5.9	8.0	1.0	9.1	1.0	9.1	
		C_L = 50 pF		7.4	10.0	1.0	11.1	1.0	11.1	
t_{PLZ}	Output Disable Time RCK to QA−QH Output Enable Time RCK to QA−QH	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF		7.7	11.9	1.0	13.5	1.0	13.5	ns
		C_L = 50 pF		10.2	15.4	1.0	17.0	1.0	17.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF		5.4	7.4	1.0	8.5	1.0	8.5	
		C_L = 50 pF		6.9	9.4	1.0	10.5	1.0	10.5	
t_{PZL}	Output Disable Time RCK to QA−QH Output Enable Time RCK to QA−QH	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF		7.7	11.9	1.0	13.5	1.0	13.5	ns
		C_L = 50 pF		10.2	15.4	1.0	17.0	1.0	17.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF		5.4	7.4	1.0	8.5	1.0	8.5	
		C_L = 50 pF		6.9	9.4	1.0	10.5	1.0	10.5	
t_{PZL}	Output Enable Time, $\overline{OE}$ to QA−QH	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF R_L = 1 kΩ		7.5	11.5	1.0	13.5	1.0	13.5	ns
		C_L = 50 pF		9.0	15.0	1.0	17.0	1.0	17.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF R_L = 1 kΩ		4.8	8.6	1.0	10.0	1.0	10.0	
		C_L = 50 pF		8.3	10.6	1.0	12.0	1.0	12.0	
t_{PLZ}	Output Disable Time, $\overline{OE}$ to QA−QH	V_{CC} = 3.3 ± 0.3 V C_L = 50 pF R_L = 1 kΩ		12.1	15.7	1.0	16.2	1.0	16.2	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 50 pF R_L = 1 kΩ		7.6	10.3	1.0	11.0	1.0	11.0	
C_{IN}	Input Capacitance			4	10		10		10	pF
C_{OUT}	Three−State Output Capacitance (Output in High−Impedance State), QA−QH			6			10		10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 2)	87	pF

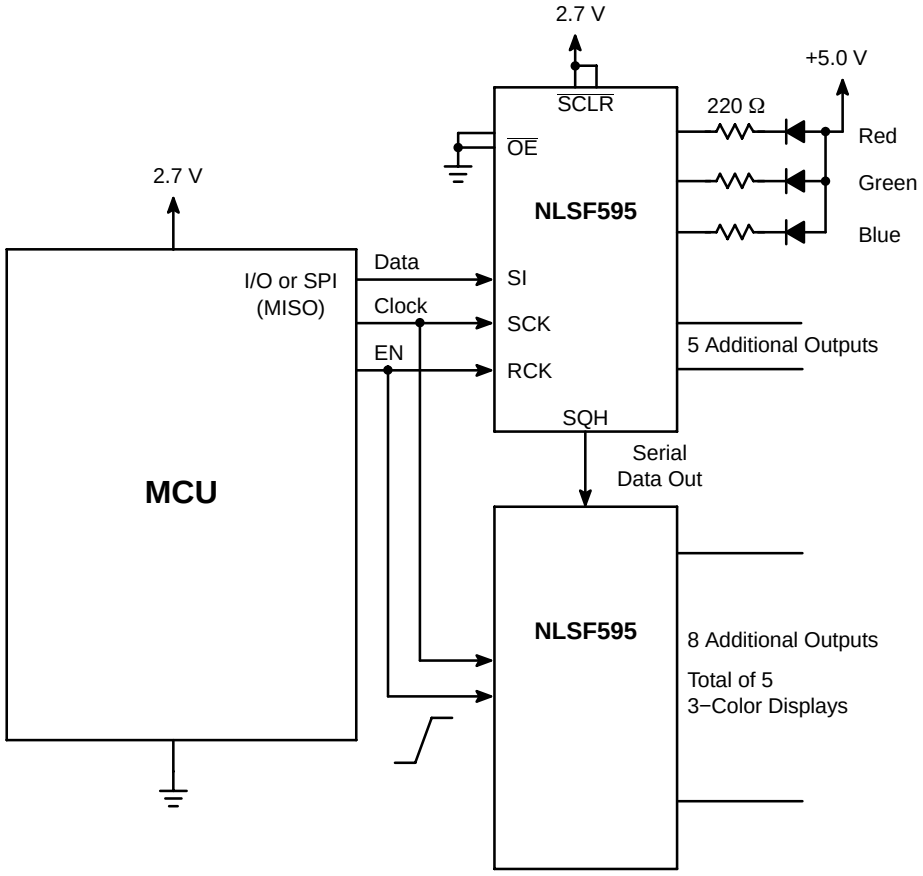
2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

Symbol	Characteristic	$T_A = 25°C$ Typ	$T_A = 25°C$ Max	Unit
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.8	1.0	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.8	−1.0	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	V_{CC} V	T_A = 25°C		T_A = − 40 to 85°C	T_A = − 55 to 125°C	Unit
			Typ	Limit	Limit	Limit	
t_{su}	Setup Time, SI to SCK	3.3 5.0		3.5 3.0	3.5 3.0	3.5 3.0	ns
$t_{su(H)}$	Setup Time, SCK to RCK	3.3 5.0		8.0 5.0	8.5 5.0	8.5 5.0	ns
$t_{su(L)}$	Setup Time, $\overline{SCLR}$ to RCK	3.3 5.0		8.0 5.0	9.0 5.0	9.0 5.0	ns
t_h	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	1.5 2.0	ns
$t_{h(L)}$	Hold Time, $\overline{SCLR}$ to RCK	3.3 5.0		0 0	0 0	1.0 1.0	ns
t_{rec}	Recovery Time, $\overline{SCLR}$ to SCK	3.3 5.0		3.0 2.5	3.0 2.5	3.0 2.5	ns
t_w	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns
$t_{w(L)}$	Pulse Width, $\overline{SCLR}$	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns



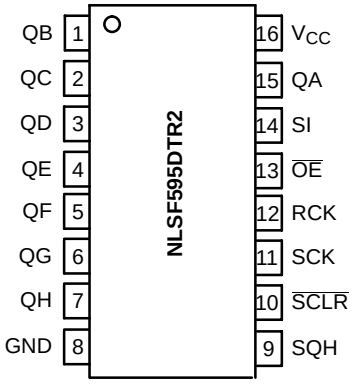


Figure 5. NLSF595 Shown Driving 5 3−Color LEDs

SWITCHING WAVEFORMS

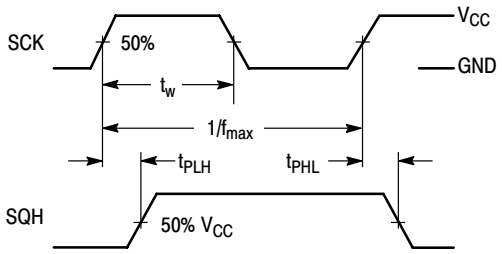


Figure 6.

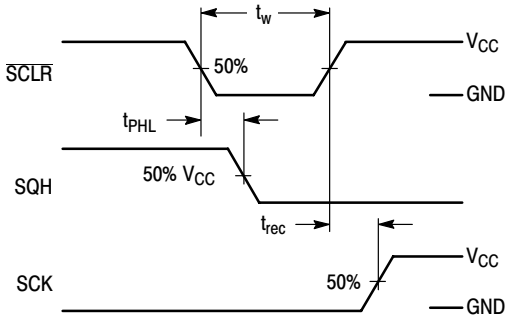


Figure 7.

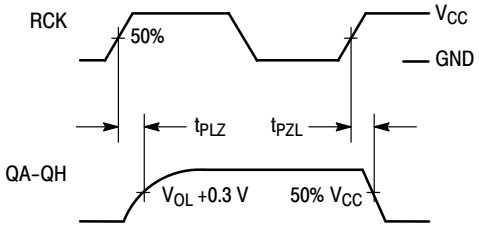


Figure 8.

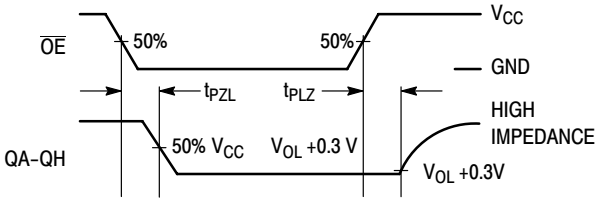


Figure 9.

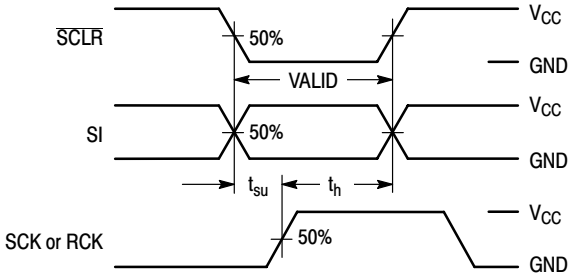


Figure 10.

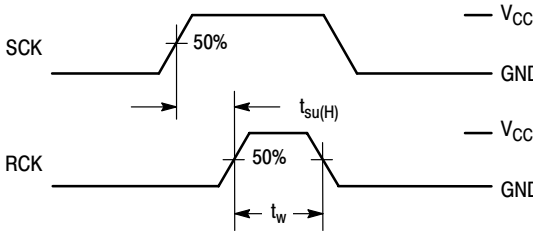
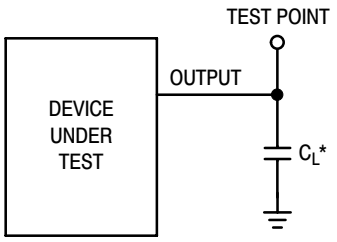


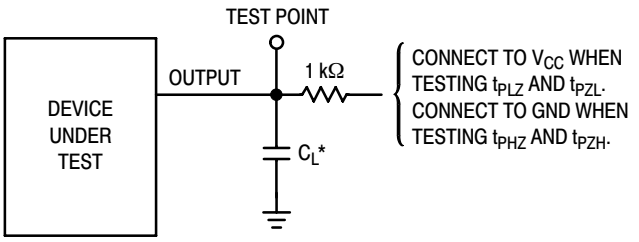
Figure 11.

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 12.



*Includes all probe and jig capacitance

Figure 13.

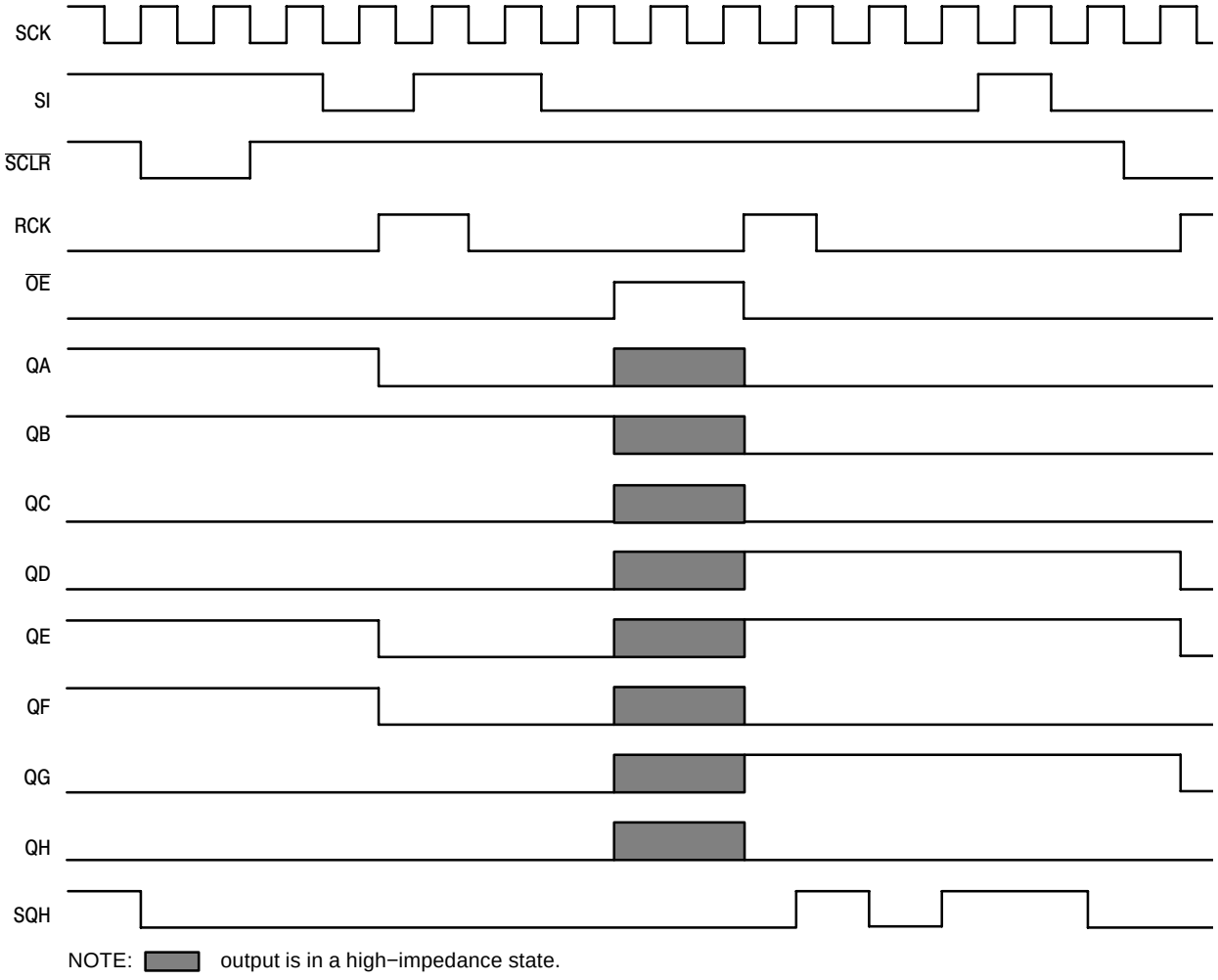


Figure 14. Timing Diagram

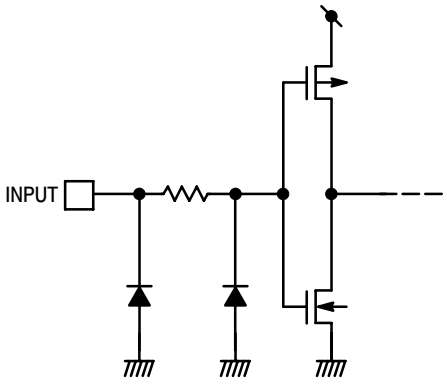


Figure 15. Input Equivalent Circuit

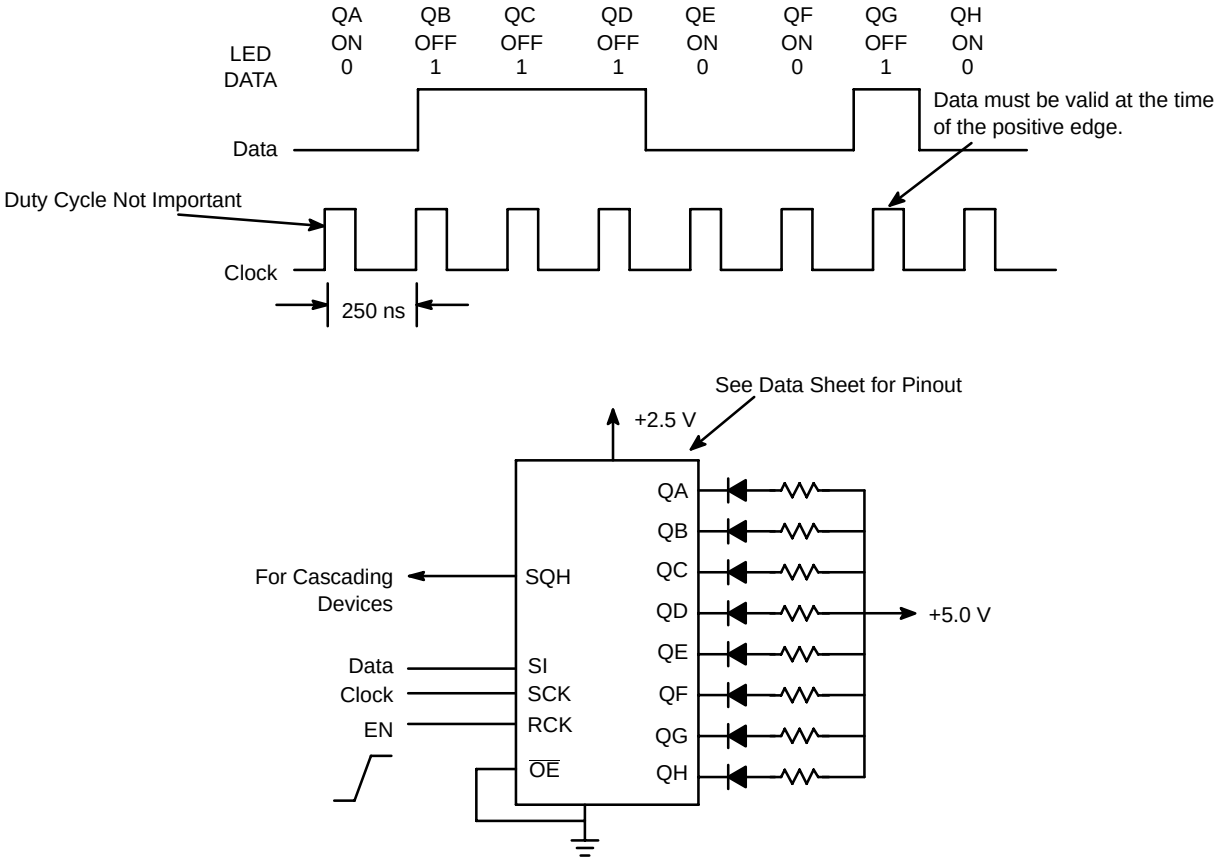


Figure 16. NLSF595 Example

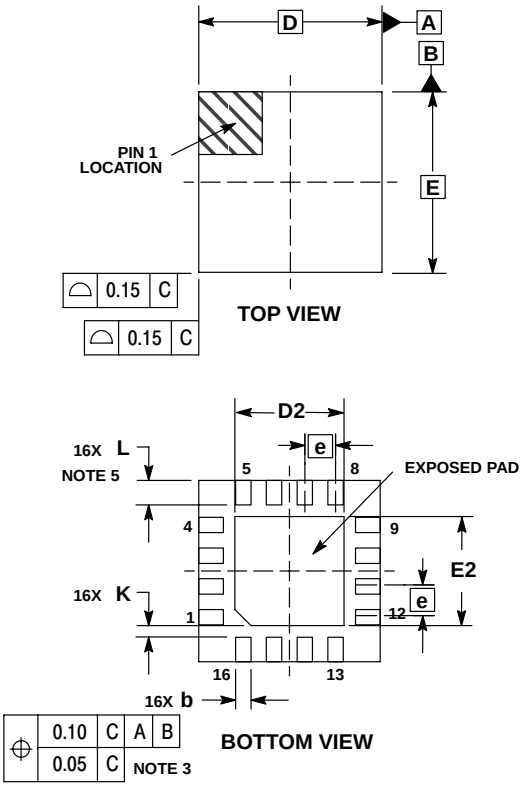
ORDERING INFORMATION

Device Order Number	Device Nomenclature					Package	Shipping†
	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix		
NLSF595MNR2	NL	SF	595	MN	R2	QFN	13−inch/2500 Unit
NLSF595MNR2G	NL	SF	595	MN	R2	QFN (Pb−Free)	13−inch/2500 Unit
NLSF595DTR2	NL	SF	595	DT	R2	TSSOP* (Pb−Free)	13−inch/2500 Unit

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

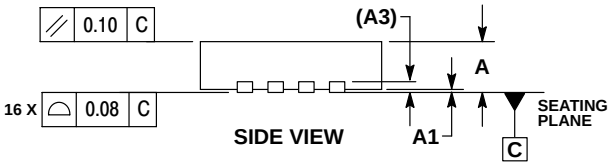
PACKAGE DIMENSIONS

QFN−16
MN SUFFIX
CASE 485G−01
ISSUE B

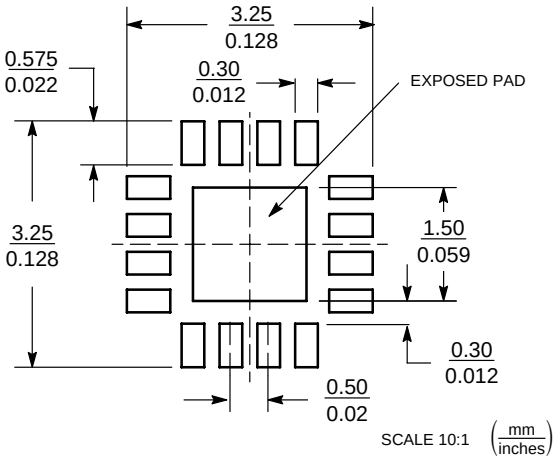


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. L_{max} CONDITION CAN NOT VIOLATE 0.2 MM MINIMUM SPACING BETWEEN LEAD TIP AND FLAG

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.18	0.30
D	3.00 BSC	
D2	1.65	1.85
E	3.00 BSC	
E2	1.65	1.85
e	0.50 BSC	
K	0.20	−−−
L	0.30	0.50



SOLDERING FOOTPRINT*

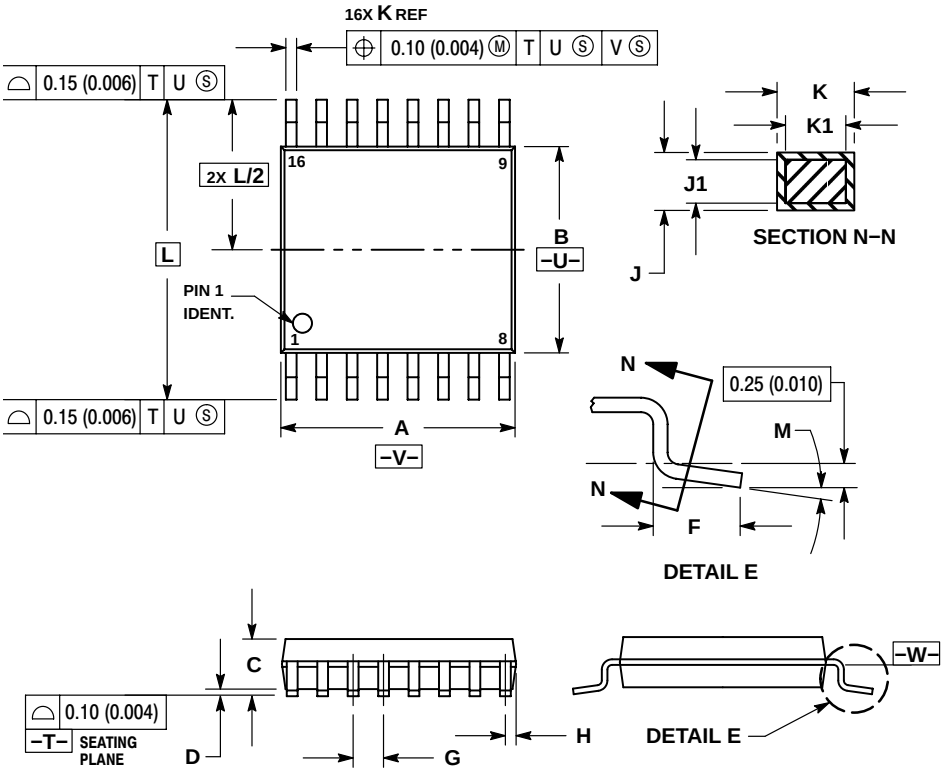


*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NLSF595

PACKAGE DIMENSIONS

TSSOP−16
DT SUFFIX
CASE 948F−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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